

PMEGxx05ET series

0.5~A very low V_F MEGA Schottky barrier rectifiers in SOT23 package

Rev. 02 — 13 January 2010

Product data sheet

1. Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOT23 small Surface Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package		Configuration
	NXP	JEITA	
PMEG2005ET	SOT23	-	single diode
PMEG3005ET	SOT23	-	single diode
PMEG4005ET	SOT23	-	single diode

1.2 Features

- Forward current: 0.5 A
- Very low forward voltage
- Small SMD plastic package

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Inverse polarity protection
- Low power consumption applications



1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	forward current		-	-	0.5	Α
V _R	reverse voltage					
	PMEG2005ET		-	-	20	V
	PMEG3005ET		-	-	30	V
	PMEG4005ET		-	-	40	V
V _F	forward voltage	$I_F = 500 \text{ mA}$	<u>[1]</u>			
	PMEG2005ET		-	355	390	mV
	PMEG3005ET		-	380	430	mV
	PMEG4005ET		-	420	470	mV

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

Pinning information 2.

Table 3. **Pinning**

Pin	Description	Simplified outline	Symbol
1	anode		
2	not connected	3	1 2
3	cathode	1 2	3 mlc357

Ordering information

Ordering information Table 4.

Type number	Package	Package				
	Name	Description	Version			
PMEG2005ET	-	plastic surface mounted package; 3 leads	SOT23			
PMEG3005ET	-	plastic surface mounted package; 3 leads	SOT23			
PMEG4005ET	-	plastic surface mounted package; 3 leads	SOT23			

Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PMEG2005ET	P3*
PMEG3005ET	P4*
PMEG4005ET	P5*

^{* = -:} made in Hong Kong

Limiting values

Table 6. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{R}	reverse voltage				
	PMEG2005ET		-	20	V
	PMEG3005ET		-	30	V
	PMEG4005ET		-	40	V
I _F	forward current		-	0.5	Α
I _{FRM}	repetitive peak forward current	$t_p \leq 1 \text{ ms; } \delta \leq 0.5$	-	3.9	Α
I _{FSM}	non-repetitive peak forward current	t _p = 8 ms square wave	<u>[1]</u> _	10	Α
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[1] -	280	mW
			[2] _	420	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard

Thermal characteristics

Thermal characteristics Table 7.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1][2]	-	440	K/W
	junction to ambient		[1][3]	-	300	K/W

For Schottky barrier diodes thermal run-away has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determining the reverse power losses P_R and I_{F(AV)} rating will be available on request.

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^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

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7. Characteristics

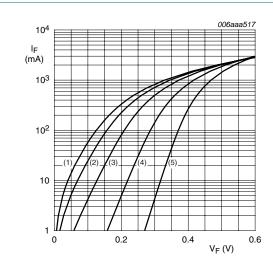
Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F	forward voltage		<u>[1]</u>			
	PMEG2005ET	$I_F = 0.1 \text{ mA}$	-	90	130	mV
		I _F = 1 mA	-	150	190	mV
		I _F = 10 mA	-	210	240	mV
		I _F = 100 mA	-	280	330	mV
		$I_F = 500 \text{ mA}$	-	355	390	mV
	PMEG3005ET	$I_F = 0.1 \text{ mA}$	-	90	130	mV
		I _F = 1 mA	-	150	200	mV
		$I_F = 10 \text{ mA}$	-	215	250	mV
		I _F = 100 mA	-	285	340	mV
		$I_F = 500 \text{ mA}$	-	380	430	mV
	PMEG4005ET	$I_F = 0.1 \text{ mA}$	-	95	130	mV
		I _F = 1 mA	-	155	210	mV
		$I_F = 10 \text{ mA}$	-	220	270	mV
		$I_F = 100 \text{ mA}$	-	295	350	mV
		$I_F = 500 \text{ mA}$	-	420	470	mV
R	reverse current					
	PMEG2005ET	V _R = 10 V	-	15	40	μΑ
		V _R = 20 V	-	40	200	μΑ
	PMEG3005ET	V _R = 10 V	-	12	30	μΑ
		$V_R = 30 \text{ V}$	-	40	150	μΑ
	PMEG4005ET	$V_R = 10 V$	-	7	20	μΑ
		V _R = 40 V	-	30	100	μΑ
C_d	diode capacitance	$V_R = 1 V$; $f = 1 MHz$				
	PMEG2005ET		-	66	80	pF
	PMEG3005ET		-	55	70	pF
	PMEG4005ET		-	43	50	рF

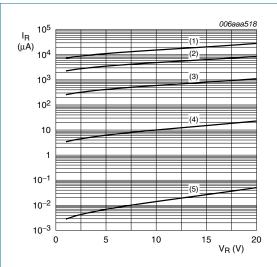
^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02$.

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- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) T_{amb} = 125 °C
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \, ^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

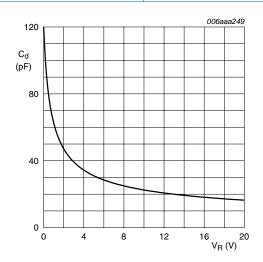
Fig 1. PMEG2005ET: Forward current as a function of forward voltage; typical values



- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \, ^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

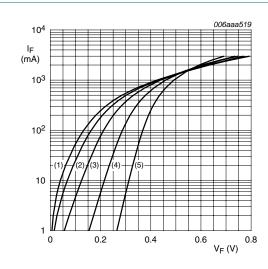
Fig 2. PMEG2005ET: Reverse current as a function of reverse voltage; typical values

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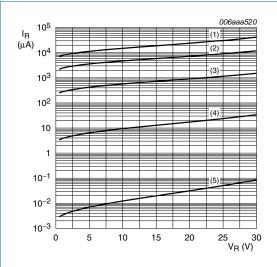
 $T_{amb} = 25 \, ^{\circ}C; f = 1 \, MHz$

Fig 3. PMEG2005ET: Diode capacitance as a function of reverse voltage; typical values



- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) T_{amb} = 125 °C
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \, ^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

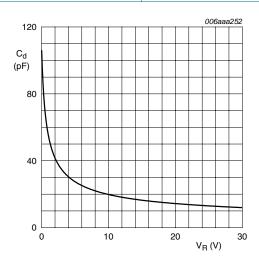
Fig 4. PMEG3005ET: Forward current as a function of forward voltage; typical values



- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \, ^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

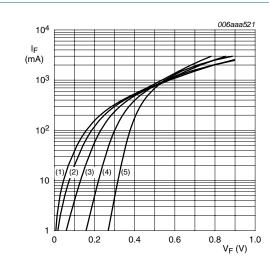
Fig 5. PMEG3005ET: Reverse current as a function of reverse voltage; typical values

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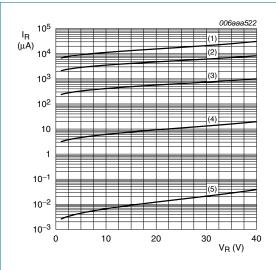
 $T_{amb} = 25 \, ^{\circ}C; f = 1 \, MHz$

Fig 6. PMEG3005ET: Diode capacitance as a function of reverse voltage; typical values



- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) T_{amb} = 125 °C
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \, ^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

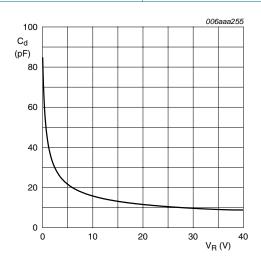
Fig 7. PMEG4005ET: Forward current as a function of forward voltage; typical values



- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \, ^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

Fig 8. PMEG4005ET: Reverse current as a function of reverse voltage; typical values

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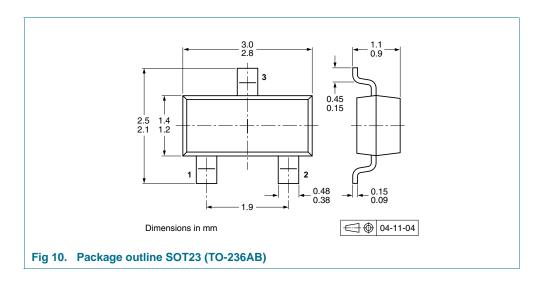
 $T_{amb} = 25 \, ^{\circ}C; f = 1 \, MHz$

Fig 9. PMEG4005ET: Diode capacitance as a function of reverse voltage; typical values

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Package outline



Packing information

Table 9. **Packing methods**

The -xxx numbers are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	quantity
			3000	10000
PMEG2005ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235
PMEG3005ET				
PMEG4005ET				

[1] For further information and the availability of packing methods, see Section 13.

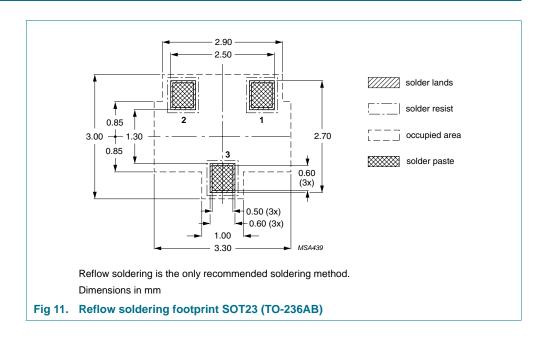
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10. Soldering

Product data sheet

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11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEGXX05ET_SER_2	20100113	Product data sheet	-	PMEGXX05ET_SER_1
Modifications:	including ne- content.	eet was changed to reflect w legal definitions and disc eflow soldering footprint SO	aimers. No changes w	rere made to the technical
PMEGXX05ET_SER_1	20050715	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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